



850nm GaAs PIN Photodiode in TO-46 Package for 850nm Emitter

Part No. PDT-A85A30

Features

- Industry standard TO-46 package with cap lens
- Optimized for fiber optic application
- High coupling efficiency to multi-mode fibers directly
- Low dark current and low capacitance
- Bandwidth >1.5 GHz



Specifications

Absolute Maximum Ratings				
Parameters	Min.	Max.	Unit	Conditions
Storage temperature	-40	125	°C	
Operating temperature	-20	85	°C	
Lead solder temperature		260	°C	10 seconds

Electro-Optical Characteristics						
Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Responsivity ⁽¹⁾	R	-	0.3	0.4	A/W	V _R =5V, λ=850 nm
Forward Current	I _F	100	-	-	μA	V _F =1V
Dark Current	I _D	-	1	2	nA	V _R =5V
Breakdown Voltage	V _{BD}	-	85	-	V	I _R =10μA
Capacitance ⁽²⁾	C	-	1.2	1.5	pF	V _R =5V, f=1 MHz

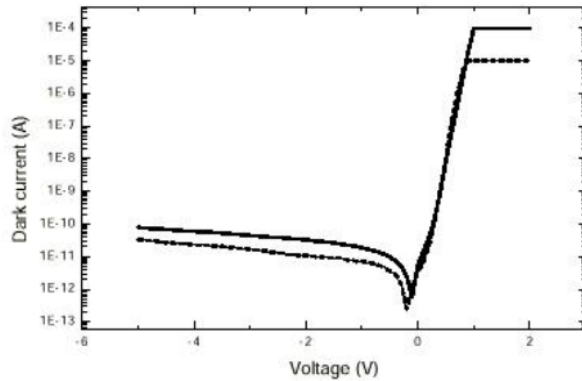
Notes:

1. The responsivity is measured with a receptacle package, using an 850 nm VCSEL as the optical light source to the 50/125 or 62.5/125μm multi-mode fibers.
2. Sensitive area is typical 120μm in diameter.

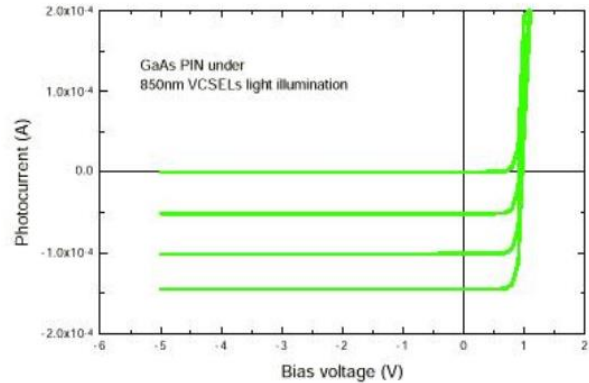


Typical Characteristics

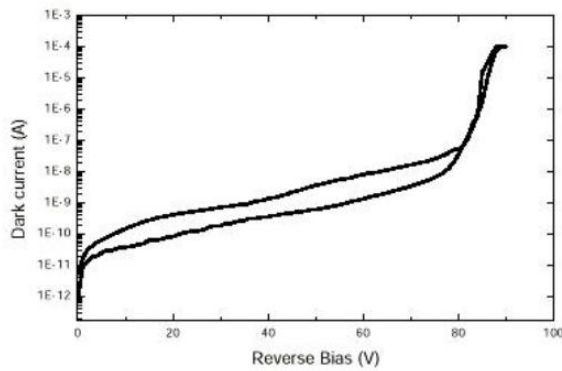
Typical Dark Current vs. Forward Current



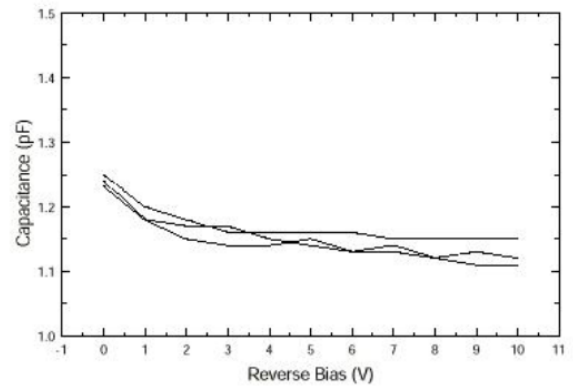
Typical Photo-Current



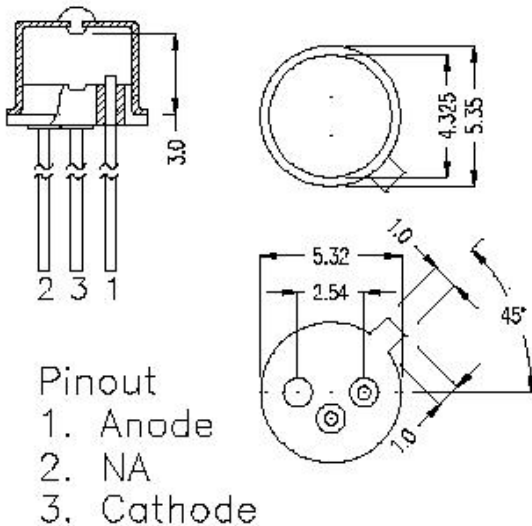
Typical Breakdown Curve



Typical C-V Curve



Outline Dimensions (unit: mm)



Note: Specifications are subject to change without notice.